

Epi - Wafer

n-Type GaN



Feature	n-Type GaN Epi. Wafer Single side polished (Growth surface)
Diameter	2" (50.8mm)
Thickness (Included substrate)	430 μ m $\pm$ 15 μ m
Structure	n-GaN / u-GaN / Sapphire substrate



GaN on Sapphire Wafer

Characteristics (at 25°C)

Parameter		Typ.	Test Conditions
PL measurement	Peak wavelength	362nm $\pm$ 2nm	Etamax PLATO Laser : 266nm
	Uniformity STD	<3%	
	FWHM	<10nm	
	FWHM STD	<3%	
Thickness	Thickness	$\sim 4\mu$ m (+/-10% std)	
	Thickness STD	<10%	
XRD	(002)	<400 arcsec	Panalytical HRXRD
	(102)	<500 arcsec	
Hall	Carrier Concentration	$\geq -1 \times 10^{18}$ /cm ³	Accent HL5500
	Mobility	≤ 200 cm ² /V-sec	
Doping material	Si	used	-
	Mg	N/A	

Normalized Single Spectrum(300 ~ 700nm)

